from knowledge generation to science-based innovation





INSTITUTE FOR SYSTEMS AND COMPUTER ENGINEERING, TECHNOLOGY AND SCIENCE

OPEN CTM

Memristors for Neuromorphic Computing

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CENIMAT

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Current Status

- Edge:
 - Interface with real world
- Computing at the edge improves:
 - Privacy
 - Latency
- •Artificial intelligence (AI) on the Edge — Edge AI
 - Inference
 - Machine Learning





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Al of today and tomorrow

Modern age Al

- Al algorithms
- Big data
- Communication networks
- Powerful computing hardware (CMOS on the frontline)

Next generation AI

- Self-Learning
- One step learning
- Cognition
- New hardware paradigms

Classical Central Processing





On the way for the next AI generation

Near Memory Computating



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On the way for the next AI generation

Neuromorphic computing

- Brain Inspired
- Event-based processing
- SNNs



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Synaptic Learning — Spike Time Dependent Plasticity (STDP)

- Neurons fire pulses
- Weights (synapses) are updated based on time difference between post- and pre-synaptic pulses
- These properties have been demonstrated with memristor like devices



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NeurOxide



New computer paradigms to overcome Von Neumann's bottleneck



\rightarrow Memristors learn and forget like biological synapses

Aims to achieve a fully integrated system with memristors and supporting electronics with the same materials — amorphous oxide semiconductors (AOS) —

- Same processing steps for transistors and resistive switching devices
- Less interface issues
- Low-temperature fabrication process
- Low cost



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NeurOxide





NeurOxide — synaptic learning — IGZO thin-film memristors

Post-synaptic

Resistive switching emulates synaptic learning (weighting)

- Potentiation decreases resistance / increases conductance (Δt >0 \mapsto Positive pulse)
- Depression increases resistance / decreases conductance ($\Delta t < 0 \mapsto Negative pulse$)





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NeurOxide — Memristor Modelling — Black Box



$$I_M(t) = G_M(w,V) imes V(t)$$

$$rac{\partial w}{\partial t} = f(w,V) imes g(w,V)$$

$$G_M(w,V)$$
 Conductance

$$egin{aligned} g(w,V) & extsf{Window Function} \ f(w,V) & extsf{Threshold Function} \end{aligned}$$

Multistep Neural Networks (MSNN)

- ANN that captures the underlined ODE of the system by learning from the numerical multistep integration algorithms -





Layers





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PhD. Students: Maria Pereira & Guilherme Carvalho

NeurOxide — in-memory computation logic

vcond vset

Imply or Material Implication Logic



VCOND **VSET** Ρ R_G



vclear



nfet

W=40u

L=20u

in -



nfet

nfet

inA –

W=20u

L = 20u

inB-set^{n<u>fe</u>}

cond

clear

20set addrli

cond addr i

clear addr i

out



nfet W=20u L = 20u

M2

nfet

W=80u L=20u **M**1

gind_sig

--set_out i

gnoosig addri

cond_out i

clear out i

gnd out i

W=20

W=80 =20

inA

inB

Control circuit

-out

MSc. Student: Luís Outeiro

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Conclusion

Next Generation AI

- Self-Learning
- One step learning
- Cognition

New possible Hardware Paradigms

- In-memory computating
- Event based computation (SNNs)



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